Vishay Siliconix

P-Channel 60 V (D-S), 175 °C MOSFET



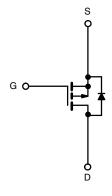
| PRODUCT SUMMARY | | | | |
|---|--------|--|--|--|
| V _{DS} (V) | -60 | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V | 0.015 | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$ | 0.020 | | | |
| I _D (A) ^d | -50 | | | |
| Configuration | Single | | | |

FEATURES

- TrenchFET® power MOSFET
- 175 °C junction temperature



 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



P-Channel MOSFET

| ORDERING INFORMATION | | |
|----------------------|-----------------|--|
| Package | DPAK (TO-252) | |
| Lead (Pb)-free | SUD50P06-15L-E3 | |

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | |
|--|-------------------------|-----------------|------------------|---------------------------------------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | V _{DS} | -60 | V |
| Gate-source voltage | | V _{GS} | ± 20 | \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ |
| Continuous drain current (T _J = 175 °C) | T _C = 25 °C | | -50 ^d | |
| | T _C = 125 °C | I _D | -39 | |
| Pulsed drain current | | I _{DM} | -80 | A |
| Avalanche current | | I _{AR} | -50 | |
| Repetitive avalanche energy ^a | L = 0.1 mH | E _{AR} | 125 | mJ |
| Power dissipation | T _C = 25 °C | В | 136 ^c | w |
| | T _A = 25 °C | P _D | 3 b, c | |
| Operating junction and storage temperature range | | Tı, Teta | -55 to +175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------------|--------------|-------------------|---------|---------|------|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
| lunation to ambient b | t ≤ 10 s | R_{thJA} | 15 | 18 | |
| Junction-to-ambient ^b | Steady state | | 40 | 50 | °C/W |
| Junction-to-case | | R _{thJC} | 0.82 | 1.1 | |

Notes

- a. Duty cycle $\leq 1\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See SOA curve for voltage derating
- d. Package limited

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| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------------------------------|---------------------|--|------|-------|-------|------|
| Static | | | | | | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | -60 | - | - | V |
| Gate threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \mu A$ | -1 | - | -3 | V |
| Gate-body leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA |
| | | $V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$ | - | - | -1 | |
| Zero gate voltage drain current | I _{DSS} | $V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 \text{ °C}$ | - | - | -50 | μΑ |
| | | V _{DS} = -48 V, V _{GS} = 0 V, T _J = 175 °C | - | - | -150 | |
| On-state drain current ^a | I _{D(on)} | V _{DS} = -5 V, V _{GS} = -10 V | -50 | - | - | Α |
| | | V _{GS} = -10 V, I _D = -17 A | - | 0.012 | 0.015 | |
| Duning and an atota projetoma 3 | | V _{GS} = -10 V, I _D = -50 A, T _J = 125 °C | - | - | 0.025 | Ω |
| Drain-source on-state resistance a | R _{DS(on)} | V _{GS} = -10 V, I _D = -50 A, T _J = 175 °C | - | - | 0.030 | |
| | | $V_{GS} = -4.5 \text{ V}, I_D = -14 \text{ A}$ | - | 0.020 | i | |
| Forward transconductance ^a | 9 _{fs} | V _{DS} = -15 V, I _D = -17 A | - | 61 | - | S |
| Dynamic ^b | | | | | | |
| Input capacitance | C _{iss} | | - | 4950 | - | pF |
| Output capacitance | C _{oss} | V _{GS} = 0 V, V _{DS} = -25 V, f = 1 MHz | - | 480 | - | |
| Reverse transfer capacitance | C _{rss} | | - | 405 | - | |
| Total gate charge ^c | Qg | | - | 110 | 165 | |
| Gate-source charge ^c | Q _{gs} | $V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -50 \text{ A}$ | - | 19 | - | nC |
| Gate-drain charge ^c | Q _{gd} | | - | 28 | - | |
| Turn-on delay time ^c | t _{d(on)} | | - | 15 | 23 | |
| Rise time ^c | t _r | V_{DD} = -30 V, R_L = 0.6 Ω | - | 70 | 105 | |
| Turn-off delay time ^c | t _{d(off)} | $I_D \cong -50 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6 \Omega$ | - | 175 | 260 | ns |
| Fall time ^c | t _f | | - | 175 | 260 | |
| Source-Drain Diode Ratings and Ch | aracteristics (| T _C = 25 °C) ^b | | • | | |
| Continuous current | Is | | - | - | -50 | ۸ |
| Pulsed current | I _{SM} | | - | - | -80 | A |
| Forward voltage ^a | V _{SD} | $I_F = -50 \text{ A}, V_{GS} = 0 \text{ V}$ | - | 1 | 1.6 | V |
| Reverse recovery time | t _{rr} | I _F = -50 A, di/dt = 100 A/μs | _ | 45 | 70 | ns |

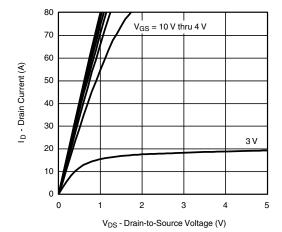
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

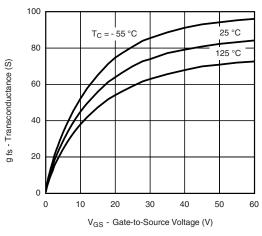
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



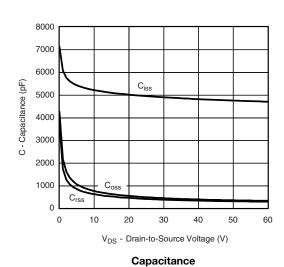
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

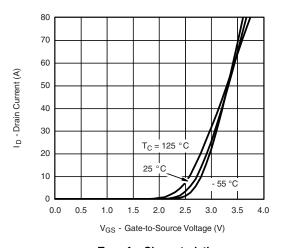


Output Characteristics

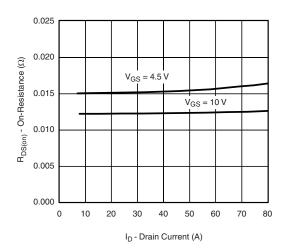


Transconductance

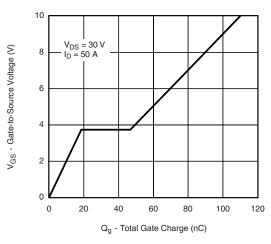




Transfer Characteristics

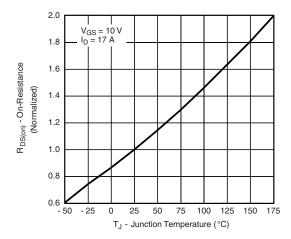


On-Resistance vs. Drain Current

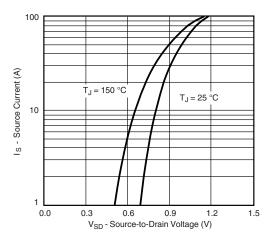




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

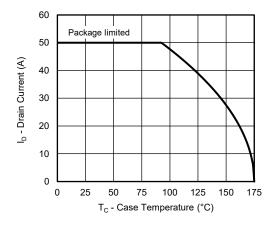


On-Resistance vs. Junction Temperature

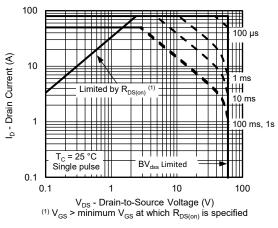


Source-Drain Diode Forward Voltage

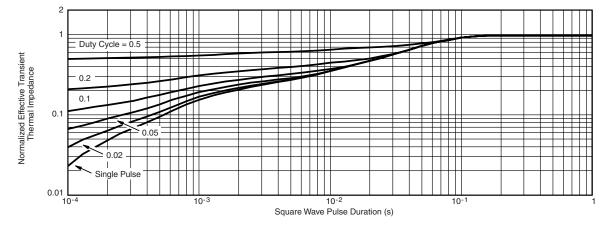
THERMAL RATINGS



Max. Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



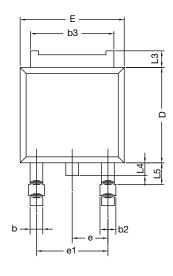
Normalized Thermal Transient Impedance, Junction-to-Case

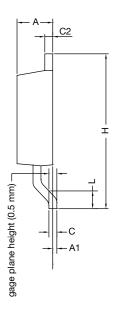
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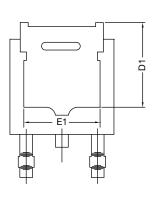


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







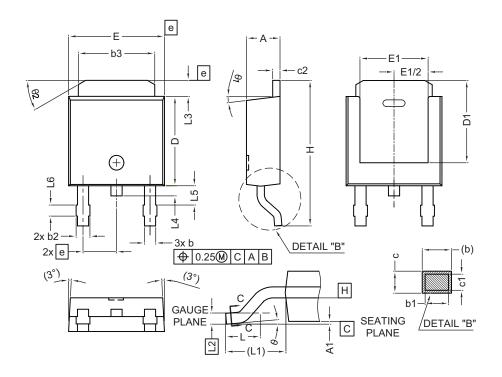
| | MILLIMETERS | | |
|------|-------------|-------|--|
| DIM. | MIN. | MAX. | |
| Α | 2.18 | 2.38 | |
| A1 | - | 0.127 | |
| b | 0.64 | 0.88 | |
| b2 | 0.76 | 1.14 | |
| b3 | 4.95 | 5.46 | |
| С | 0.46 | 0.61 | |
| C2 | 0.46 | 0.89 | |
| D | 5.97 | 6.22 | |
| D1 | 4.10 | - | |
| Е | 6.35 | 6.73 | |
| E1 | 4.32 | - | |
| Н | 9.40 | 10.41 | |
| е | 2.28 | BSC | |
| e1 | 4.56 BSC | | |
| L | 1.40 | 1.78 | |
| L3 | 0.89 | 1.27 | |
| L4 | - | 1.02 | |
| L5 | 1.01 | 1.52 | |

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



| | MILLIMETERS | | |
|------|-------------|-------|--|
| DIM. | MIN. | MAX. | |
| Α | 2.18 | 2.39 | |
| A1 | - | 0.13 | |
| b | 0.65 | 0.89 | |
| b1 | 0.64 | 0.79 | |
| b2 | 0.76 | 1.13 | |
| b3 | 4.95 | 5.46 | |
| С | 0.46 | 0.61 | |
| c1 | 0.41 | 0.56 | |
| c2 | 0.46 | 0.60 | |
| D | 5.97 | 6.22 | |
| D1 | 5.21 | = | |
| Е | 6.35 | 6.73 | |
| E1 | 4.32 | = | |
| е | 2.29 BSC | | |
| Н | 9.94 | 10.34 | |

| | MILLIMETERS | | |
|------|-------------|------|--|
| DIM. | MIN. | MAX. | |
| L | 1.50 | 1.78 | |
| L1 | 2.74 | ref. | |
| L2 | 0.51 BSC | | |
| L3 | 0.89 | 1.27 | |
| L4 | - | 1.02 | |
| L5 | 1.14 | 1.49 | |
| L6 | 0.65 | 0.85 | |
| θ | 0° | 10° | |
| θ1 | 0° | 15° | |
| θ2 | 25° | 35° | |

Notes

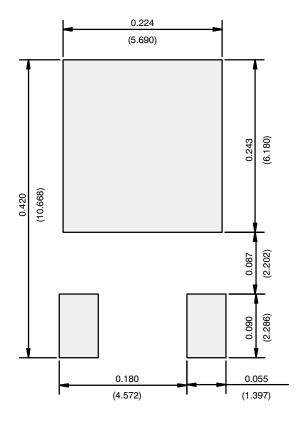
- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022

DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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